Low-power 2-input AND gate Rev. 6 — 22 June 2012

Product data sheet

General description 1.

The 74AUP1G08 provides the single 2-input AND function.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C



3. Ordering information

Table 1. Ordering	g information						
Type number	Package						
	Temperature range	Name	Description	Version			
74AUP1G08GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1			
74AUP1G08GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886			
74AUP1G08GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891			
74AUP1G08GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115			
74AUP1G08GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202			
74AUP1G08GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226			

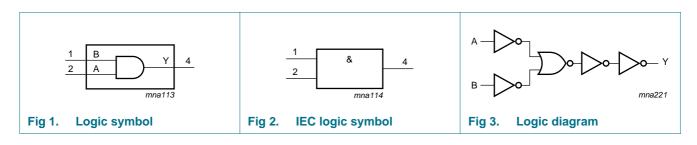
4. Marking

Table 2. Marking	J
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Type number	Marking code ^[1]
74AUP1G08GW	pE
74AUP1G08GM	pE
74AUP1G08GF	pE
74AUP1G08GN	pE
74AUP1G08GS	pE
74AUP1G08GX	pE

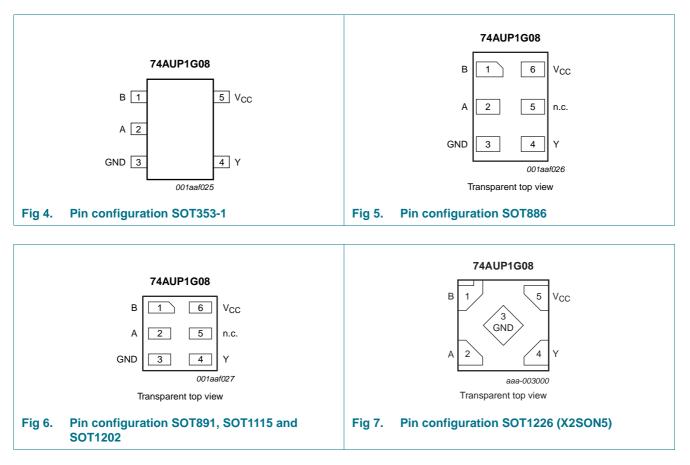
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. P	Table 3. Pin description					
Symbol	Pin		Description			
	TSSOP5 and X2SON5	XSON6				
В	1	1	data input			
A	2	2	data input			
GND	3	3	ground (0 V)			
Y	4	4	data output			
n.c.	-	5	not connected			
V _{CC}	5	6	supply voltage			

7. Functional description

Table 4.Function table^[1]

Input		Output
A	В	Y
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

[1] H = HIGH voltage level;

L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
I _O	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Recommended operating conditions					
Symbol	Parameter	Conditions	Min	Max	Unit	
V _{CC}	supply voltage		0.8	3.6	V	
VI	input voltage		0	3.6	V	
Vo	output voltage	Active mode	0	V _{CC}	V	
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V	
T _{amb}	ambient temperature		-40	+125	°C	
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V	

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.31	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V
I	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.1	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μΑ
∆I _{OFF}	additional power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μA
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.5	μA
∆I _{CC}	additional supply current		<u>[1]</u> -	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF

Low-power 2-input AND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = –	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70\times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_0 = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 imes V_{CC}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_0 = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
li i	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μΑ
∆I _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μA
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.9	μΑ
ΔI _{CC}	additional supply current		<u>[1]</u> -	-	50	μΑ

Table 7. Static characteristics ... continued

Low-power 2-input AND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-	40 °C to +125 °C			. 76	max	•
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75 \times V_{CC}$	-	-	V
• 10	in of the termination and the termination of	$V_{\rm CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.70 \times V_{CC}$		-	v
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	v
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25 \times V_{CC}$	V
• IL	2011 lotol input tokago	$V_{\rm CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.30 \times V_{CC}$	
		$V_{\rm CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{\rm CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$			0.0	-
- On		$I_{O} = -20 \ \mu A; V_{CC} = 0.8 \ V \text{ to } 3.6 \ V$	V _{CC} – 0.11	_	-	V
		$I_{O} = -1.1 \text{ mA; } V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	_	-	V
		$I_{\rm O} = -1.7 \text{ mA; } V_{\rm CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{\rm O} = -1.9 \text{ mA; } V_{\rm CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_0 = -2.3 \text{ mA; } V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{\rm O} = -3.1 \text{ mA}; V_{\rm CC} = 2.3 \text{ V}$	1.67	_	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{\rm O} = -4.0 \text{ mA}; V_{\rm CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
0L	1 0	$I_{O} = 20 \ \mu\text{A}; V_{CC} = 0.8 \ \text{V} \text{ to } 3.6 \ \text{V}$	-	-	0.11	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
1	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μA
	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.75	μΑ
∆I _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
сс	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
۵l _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	75	μΑ

Table 7. Static characteristics ... continued

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions	Min	Typ 🛄	Max	Unit
T _{amb} = 25	°C; C _L = 5 pF					
t _{pd}	propagation delay	A, B to Y; see Figure 8	[2]			
		$V_{CC} = 0.8 V$	-	17.0	-	ns
		V_{CC} = 1.1 V to 1.3 V	2.6	5.1	10.8	ns
		V_{CC} = 1.4 V to 1.6 V	1.6	3.7	6.5	ns
		V_{CC} = 1.65 V to 1.95 V	1.3	3.0	5.2	ns
		V_{CC} = 2.3 V to 2.7 V	1.1	2.4	4.0	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.2	3.5	ns
T _{amb} = 25	°C; C _L = 10 pF					
t _{pd}	propagation delay	A, B to Y; see Figure 8	[2]			
		$V_{CC} = 0.8 V$	-	20.6	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.4	6.0	12.5	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.0	4.3	7.6	ns
		V_{CC} = 1.65 V to 1.95 V	1.7	3.6	6.1	ns
		V_{CC} = 2.3 V to 2.7 V	1.4	2.9	4.8	ns
		V_{CC} = 3.0 V to 3.6 V	1.3	2.7	4.2	ns
T _{amb} = 25	°C; C _L = 15 pF					
t _{pd}	propagation delay	A, B to Y; see Figure 8	[2]			
		$V_{CC} = 0.8 V$	-	24.1	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.4	6.8	14.2	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.3	4.9	8.6	ns
		V_{CC} = 1.65 V to 1.95 V	1.9	4.0	6.9	ns
		V_{CC} = 2.3 V to 2.7 V	1.7	3.4	5.5	ns
		V_{CC} = 3.0 V to 3.6 V	1.5	3.1	4.8	ns
T _{amb} = 25	°C; C _L = 30 pF					
t _{pd}	propagation delay	A, B to Y; see Figure 8	[2]			
		$V_{CC} = 0.8 V$	-	34.4	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.6	9.1	19.4	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	3.4	6.4	11.5	ns
		V_{CC} = 1.65 V to 1.95 V	2.6	5.3	9.1	ns
		V_{CC} = 2.3 V to 2.7 V	2.3	4.5	7.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.2	4.2	6.2	ns

Low-power 2-input AND gate

Symbol	Parameter	Conditions	Min	Typ <u>1</u>	Max	Unit
T _{amb} = 25	°C					
C _{PD}	power dissipation capacitanc	e f = 1 MHz; V_I = GND to V_{CC}	[3]			
		$V_{CC} = 0.8 V$	-	2.5	-	pF
	V_{CC} = 1.1 V to 1.3 V	-	2.7	-	pF	
		V_{CC} = 1.4 V to 1.6 V	-	2.8	-	pF
		V_{CC} = 1.65 V to 1.95 V	-	2.9	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.5	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	4.0	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 f_o = output frequency in MHz;

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions		–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Max	Min	Max	
C _L = 5 pF								
t _{pd}	propagation delay	A, B to Y; see Figure 8	<u>[1]</u>					
		V_{CC} = 1.1 V to 1.3 V		2.1	11.7	2.1	12.9	ns
		V_{CC} = 1.4 V to 1.6 V		1.5	7.5	1.5	8.3	ns
		V_{CC} = 1.65 V to 1.95 V		1.3	6.1	1.3	6.7	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	4.8	1.0	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		0.9	4.3	0.9	4.8	ns
C _L = 10 pF								
t _{pd}	propagation delay	A, B to Y; see Figure 8	<u>[1]</u>					
		V_{CC} = 1.1 V to 1.3 V		2.2	13.6	2.2	15.0	ns
		V_{CC} = 1.4 V to 1.6 V		1.8	8.9	1.8	9.8	ns
		V_{CC} = 1.65 V to 1.95 V		1.6	7.2	1.6	7.9	ns
		V_{CC} = 2.3 V to 2.7 V		1.3	5.7	1.3	6.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.2	4.7	1.2	5.2	ns

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Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit	
				Min	Max	Min	Max	
C _L = 15 pl	F							
t _{pd}	propagation delay	A, B to Y; see Figure 8	<u>[1]</u>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.1	15.7	3.1	17.3	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		2.1	10.1	2.1	11.2	ns
		V_{CC} = 1.65 V to 1.95 V		1.8	8.2	1.8	9.0	ns
		V_{CC} = 2.3 V to 2.7 V		1.6	6.5	1.6	7.2	ns
		V_{CC} = 3.0 V to 3.6 V		1.5	5.9	1.5	6.5	ns
C _L = 30 p	F							
t _{pd}	propagation delay	A, B to Y; see Figure 8	<u>[1]</u>					
		V_{CC} = 1.1 V to 1.3 V		4.1	21.8	4.1	24.0	ns
		V_{CC} = 1.4 V to 1.6 V		2.9	13.6	2.9	15.0	ns
		V_{CC} = 1.65 V to 1.95 V		2.4	10.9	2.4	12.1	ns
		V_{CC} = 2.3 V to 2.7 V		2.2	8.6	2.2	9.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.1	7.5	2.1	8.3	ns

Table 9. Dynamic characteristics ... continued

-----010.6

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

12. Waveforms

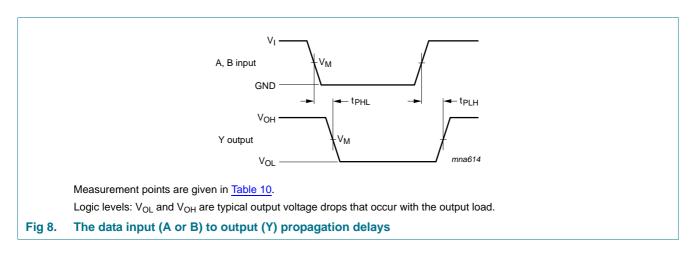


Table 10. Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	VI	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 imes V_{CC}$	V _{CC}	\leq 3.0 ns

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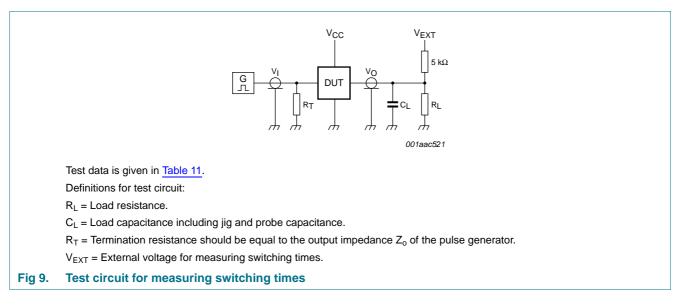


Table 11. Test data

Supply voltage	Load	V _{EXT}			
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

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13. Package outline

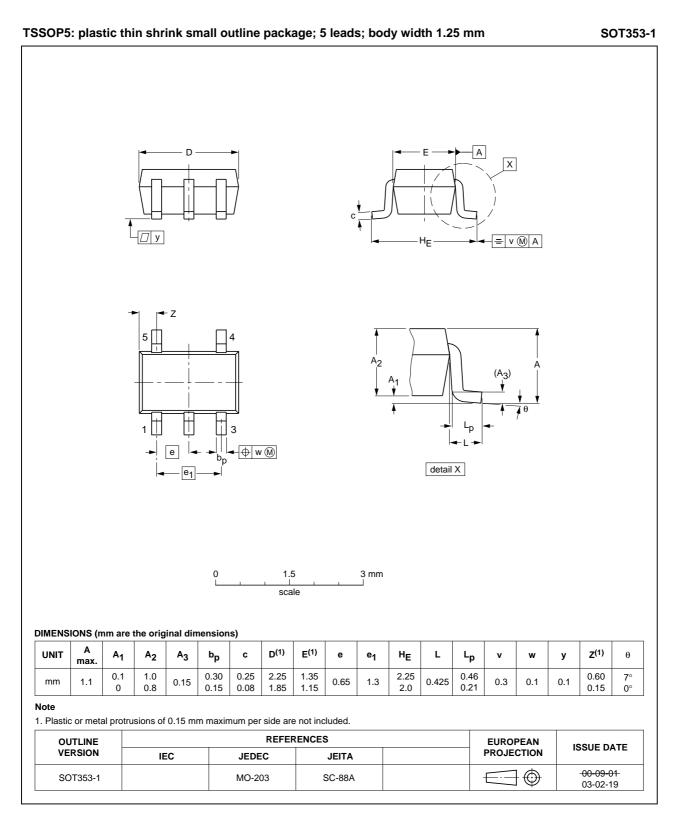
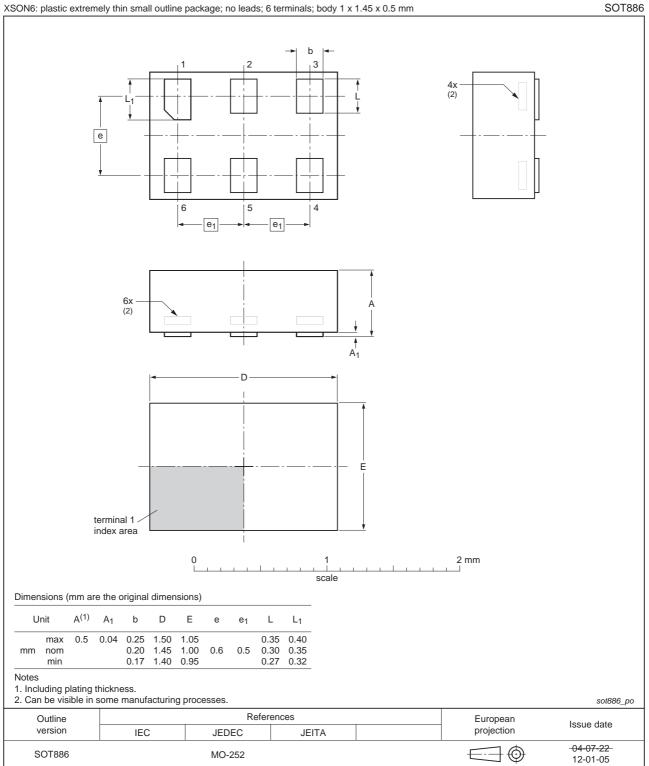


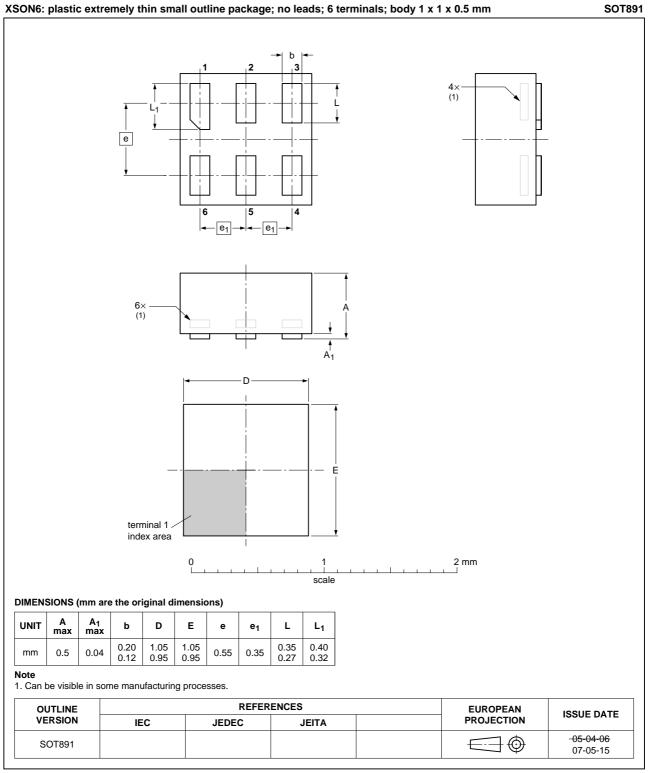
Fig 10. Package outline SOT353-1 (TSSOP5)

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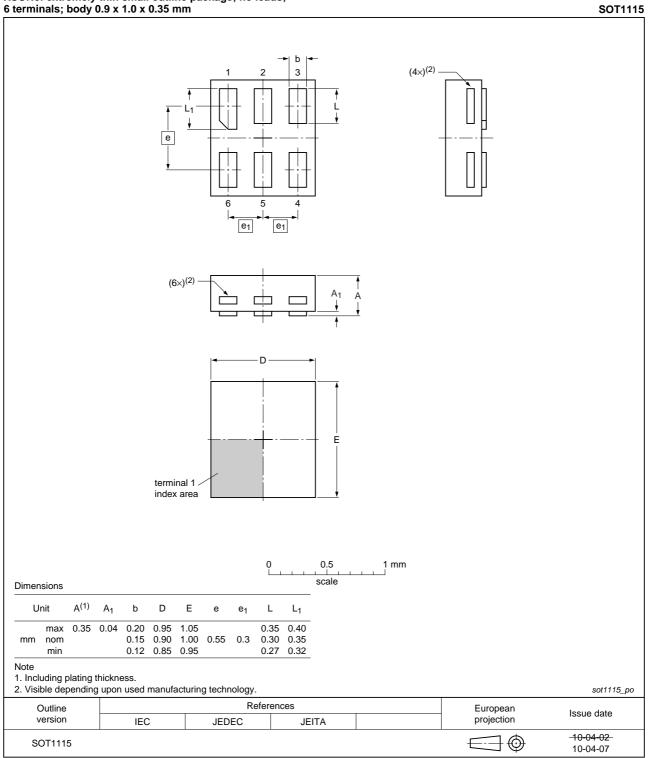
XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

Fig 11. Package outline SOT886 (XSON6)



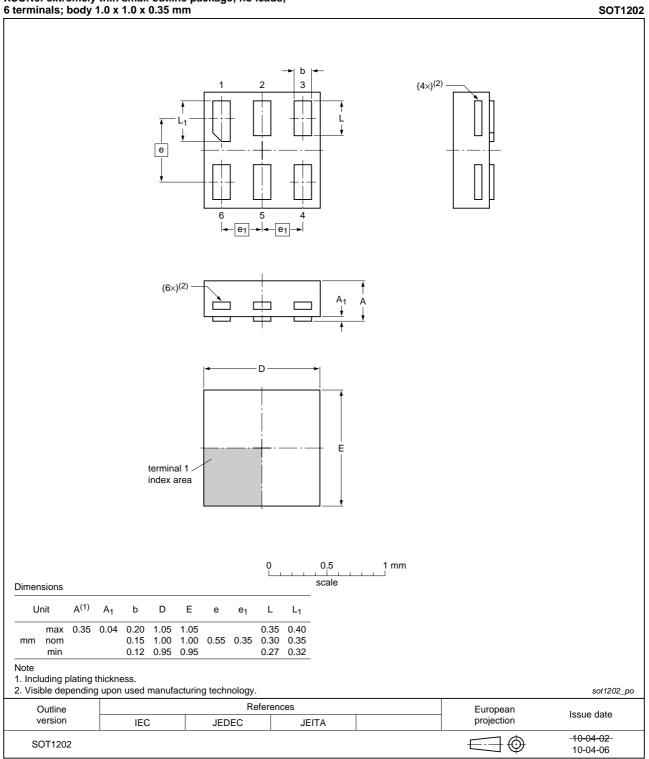
XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

Fig 12. Package outline SOT891 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

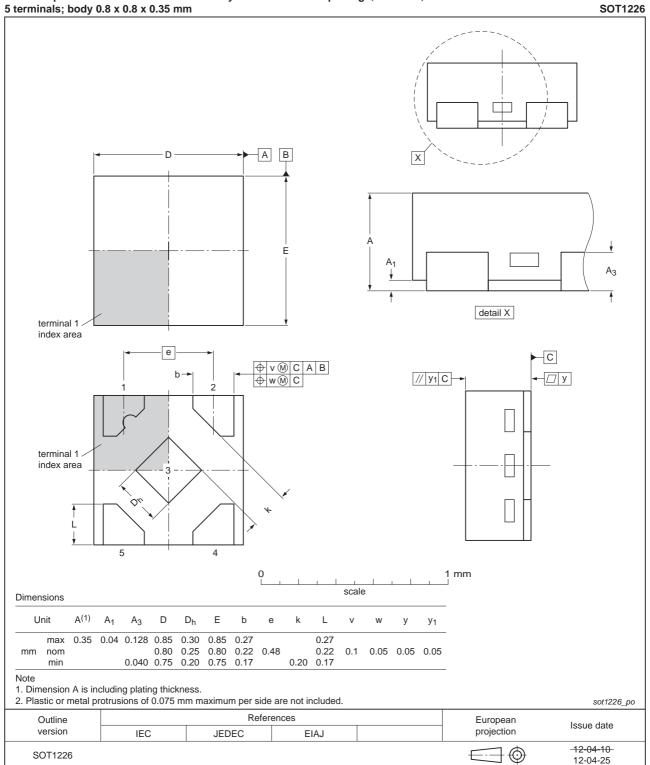
Fig 13. Package outline SOT1115 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1202 (XSON6)

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X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 x 0.8 x 0.35 mm

Fig 15. Package outline SOT1226 (X2SON5)

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14. Abbreviations

Table 12. Abbreviations				
Acronym	Description			
CDM	Charged Device Model			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			

15. Revision history

Table 13. Revisio	on history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G08 v.6	20120622	Product data sheet	-	74AUP1G04 v.5
Modifications:	 Package out 	line drawing of SOT1226 (Fig	gure 15) modified.	
74AUP1G08 v.5	20120412	Product data sheet	-	74AUP1G04 v.4
Modifications:	 Added type r 	number 74AUP1G08GX (SO	Г1226)	
	 Package out 	line drawing of SOT886 (<mark>Fig</mark>	ure 11) modified.	
74AUP1G08 v.4	20111115	Product data sheet	-	74AUP1G08 v.3
Modifications:	 Legal pages 	updated.		
74AUP1G08 v.3	20101007	Product data sheet	-	74AUP1G08 v.2
74AUP1G08 v.2	20060629	Product data sheet	-	74AUP1G08 v.1
74AUP1G08 v.1	20050720	Product data sheet	-	-



16. Legal information

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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